

isc N-Channel MOSFET Transistor

2SK2611

DESCRIPTION

- Drain Current $-I_D=9A@ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}= 900V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

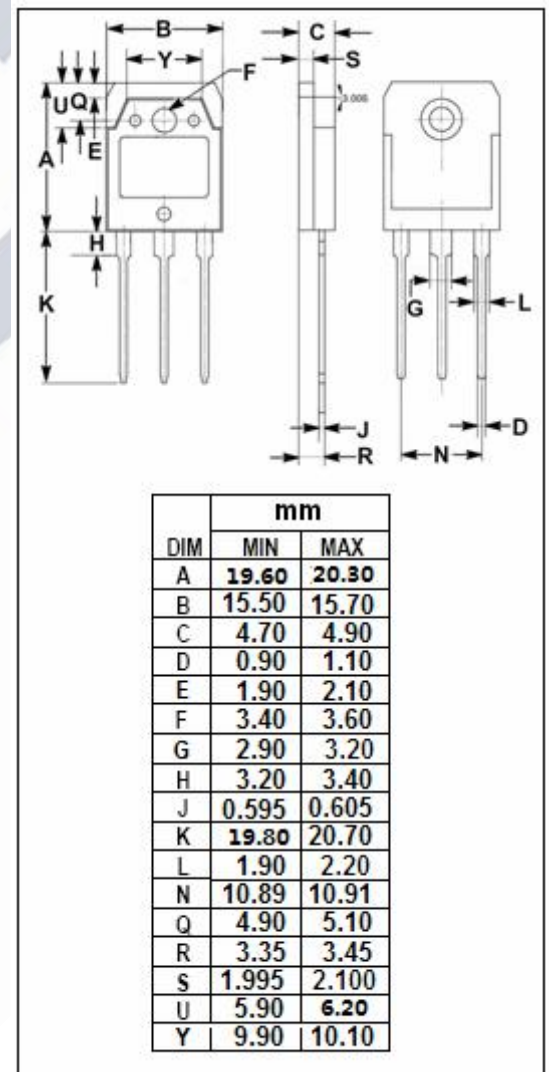
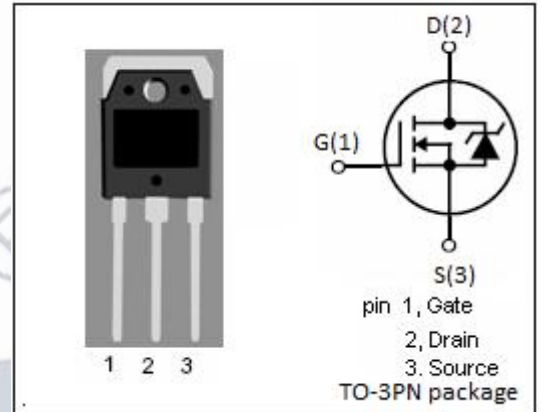
- low on-resistance.
- High speed switching.
- No secondary breakdown.
- Suitable for switching regulator, DC-DC control.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	900	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	9	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	150	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.833	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	50	$^\circ C/W$



isc N-Channel Mosfet Transistor**2SK2611****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	900			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = 10V; I _D = 1mA	2.0		4.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 4A			1.4	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =720V; V _{GS} = 0			100	uA
V _{SD}	Diode Forward Voltage	I _F = 9A; V _{GS} =0			1.9	V